

General Description

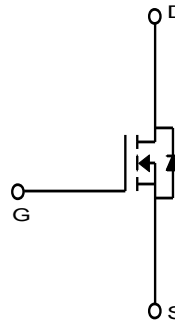
The MDIS1502 uses advanced MagnaChip's MOSFET Technology, which provides high performance in on-state resistance, fast switching performance and excellent quality. MDIS1502 is suitable device for DC to DC converter and general purpose applications.

Features

- $V_{DS} = 30V$
- $I_D = 45.7A @ V_{GS} = 10V$
- $R_{DS(ON) (MAX)} < 8.5m\Omega @ V_{GS} = 10V$
- $< 13.0m\Omega @ V_{GS} = 4.5V$
- 100% UIL Tested
- 100% Rg Tested



**TO251(VS)
(IPAK(VS))**



Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	30	V
Gate-Source Voltage		V_{GSS}	± 20	V
Continuous Drain Current ⁽¹⁾	$T_C=25^\circ C$	I_D	45.7	A
	$T_C=70^\circ C$		36.6	
	$T_A=25^\circ C$		20.4 ⁽³⁾	
	$T_A=70^\circ C$		16.3 ⁽³⁾	
Pulsed Drain Current		I_{DM}	100	A
Power Dissipation	$T_C=25^\circ C$	P_D	31.2	W
	$T_C=70^\circ C$		20.0	
	$T_A=25^\circ C$		6.2 ⁽³⁾	
	$T_A=70^\circ C$		4.0 ⁽³⁾	
Single Pulse Avalanche Energy ⁽²⁾		E_{AS}	47	mJ
Junction and Storage Temperature Range		T_J, T_{stg}	-55~150	°C

Thermal Characteristics

Characteristics	Symbol	Rating	Unit
Thermal Resistance, Junction-to-Ambient ⁽¹⁾	$R_{\theta JA}$	20.0	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	4.0	

Ordering Information

Part Number	Temp. Range	Package	Packing	Quantity	Rohs Status
MDIS1502TH	-55~150°C	TO-251-VS(IPAK)	Tube	75 units /Tube	Halogen Free

Electrical Characteristics (T_J =25°C)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	I _D = 250μA, V _{GS} = 0V	30	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1.3	1.9	2.7	
Drain Cut-Off Current	I _{DSS}	V _{DS} = 30V, V _{GS} = 0V	-	-	1	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V	-	-	±0.1	
Drain-Source ON Resistance	R _{DS(ON)}	V _{GS} = 10V, I _D = 16A	-	7.4	8.5	mΩ
		T _J =125°C	-	10.7	12.3	
Forward Transconductance	g _{fs}	V _{DS} = 5V, I _D = 10A	-	25	-	S
Dynamic Characteristics						
Total Gate Charge	Q _{g(10V)}	V _{DS} = 15.0V, I _D = 16A, V _{GS} = 10V	10.7	14.3	17.9	nC
Total Gate Charge	Q _{g(4.5V)}		5.0	6.7	8.4	
Gate-Source Charge	Q _{gs}		-	2.6	-	
Gate-Drain Charge	Q _{gd}		-	2.3	-	
Input Capacitance	C _{iss}	V _{DS} = 15.0V, V _{GS} = 0V, f = 1.0MHz	696	928	1160	pF
Reverse Transfer Capacitance	C _{rss}		68	90	113	
Output Capacitance	C _{oss}		132	176	220	
Turn-On Delay Time	t _{d(on)}	V _{GS} = 10V, V _{DS} = 15.0V, I _D = 16A, R _G = 3.0Ω	-	7.2	-	ns
Rise Time	t _r		-	12.0	-	
Turn-Off Delay Time	t _{d(off)}		-	22.8	-	
Fall Time	t _f		-	8.1	-	
Gate Resistance	R _g	f=1 MHz	-	3.5	5.0	Ω
Drain-Source Body Diode Characteristics						
Source-Drain Diode Forward Voltage	V _{SD}	I _S = 16A, V _{GS} = 0V	-	0.8	1.1	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 16A, di/dt = 100A/μs	-	20.4	30.6	ns
Body Diode Reverse Recovery Charge	Q _{rr}		-	11.9	17.9	nC

Note :

- Surface mounted FR-4 board by JEDEC (jesd51-7)
- E_{AS} is tested at starting T_j = 25 °C, L = 0.1mH, I_{AS} = 17.0A, V_{DD} = 27V, V_{GS} = 10V.
- T < 10sec.

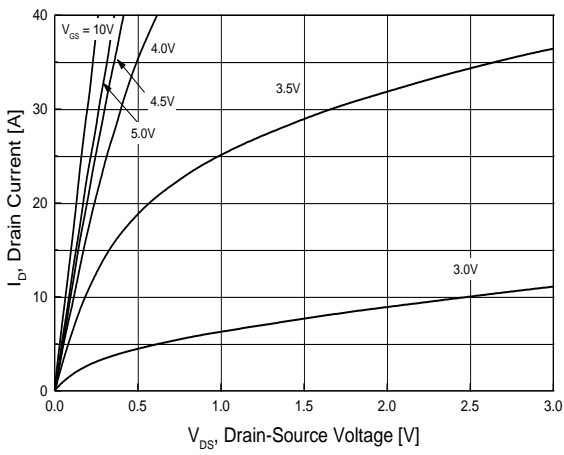


Fig.1 On-Region Characteristics

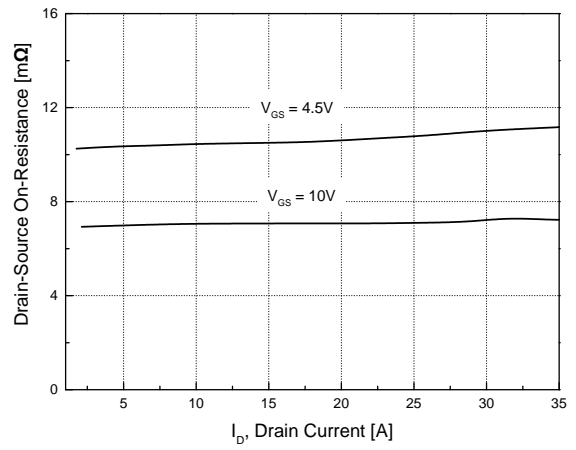


Fig.2 On-Resistance Variation with Drain Current and Gate Voltage

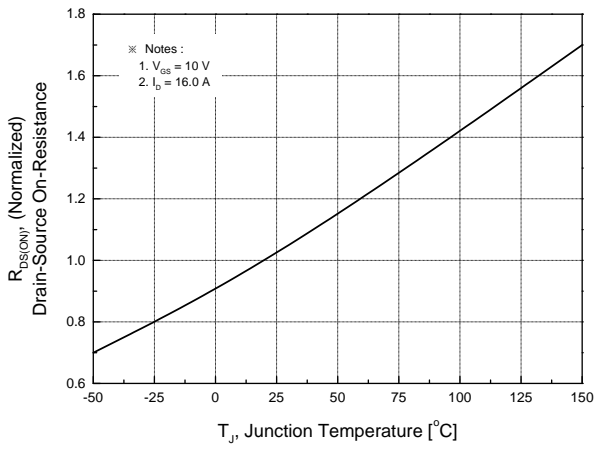


Fig.3 On-Resistance Variation with Temperature

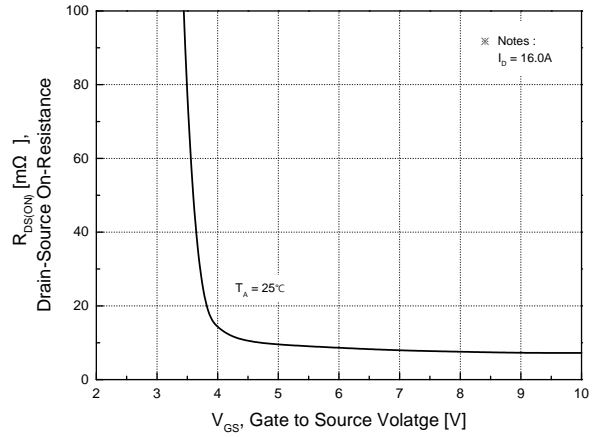


Fig.4 On-Resistance Variation with Gate to Source Voltage

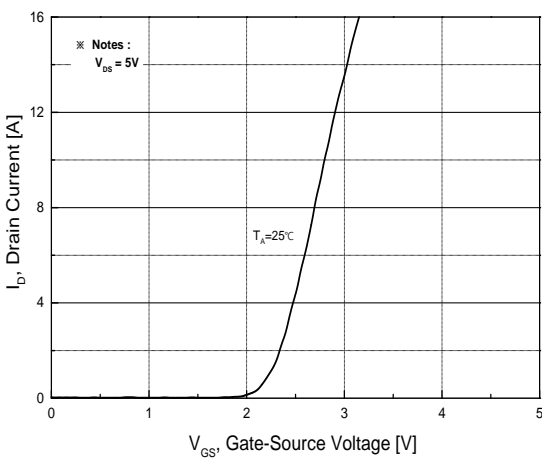


Fig.5 Transfer Characteristics

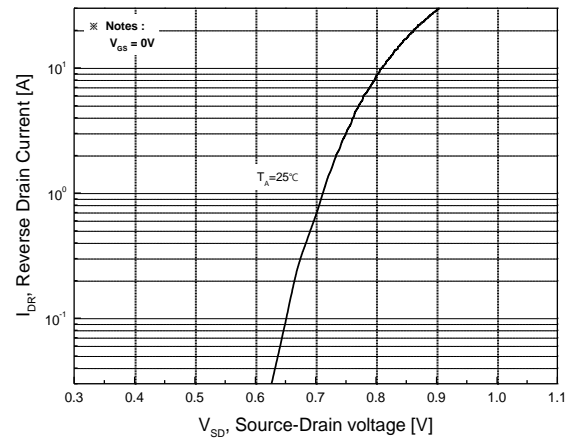
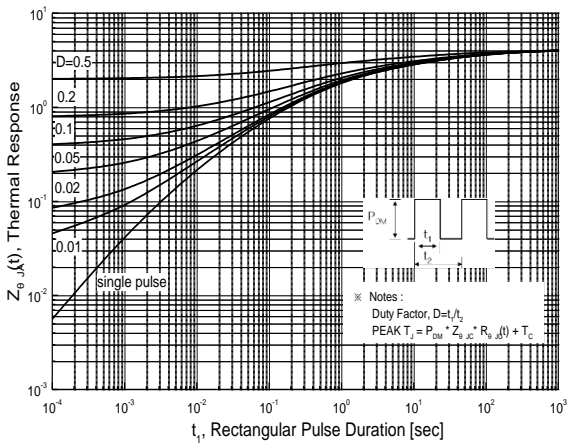
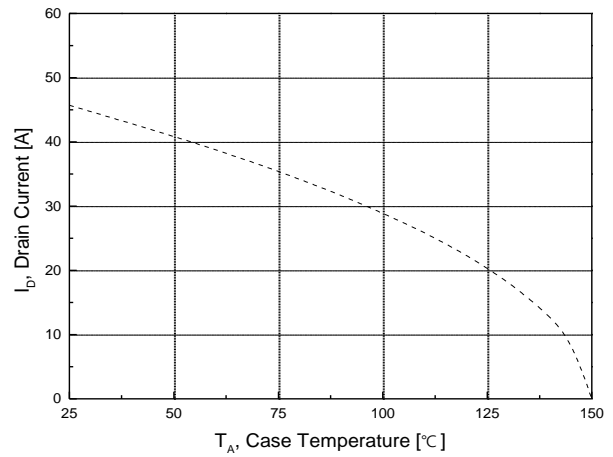
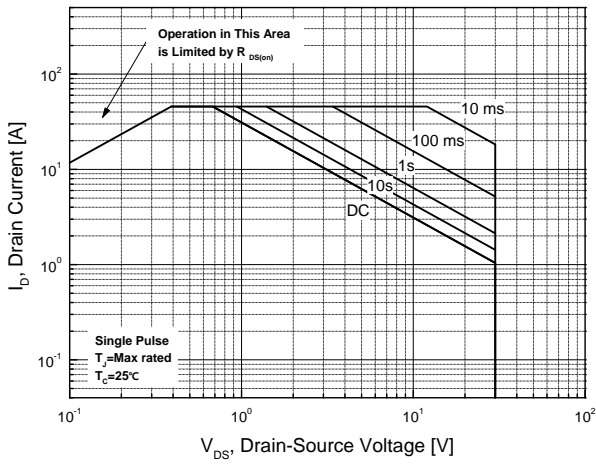
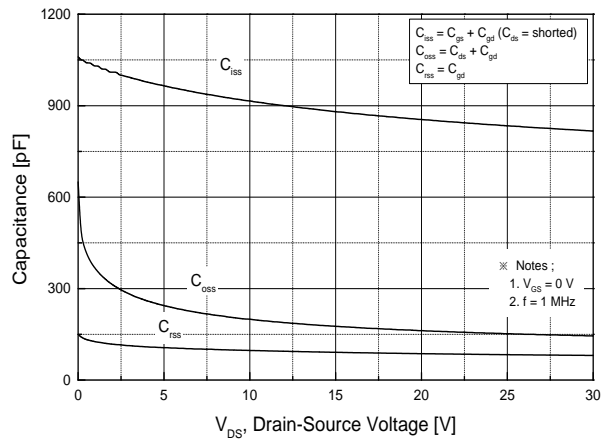
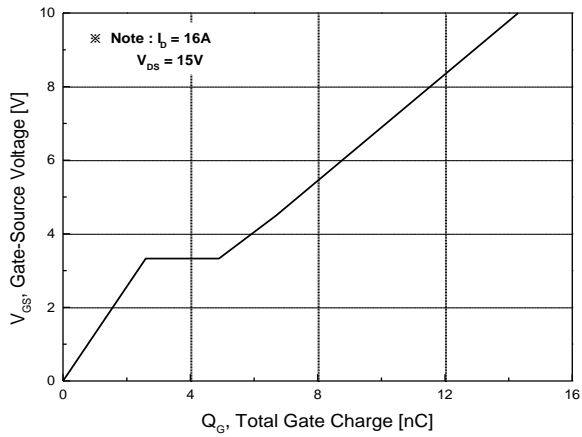
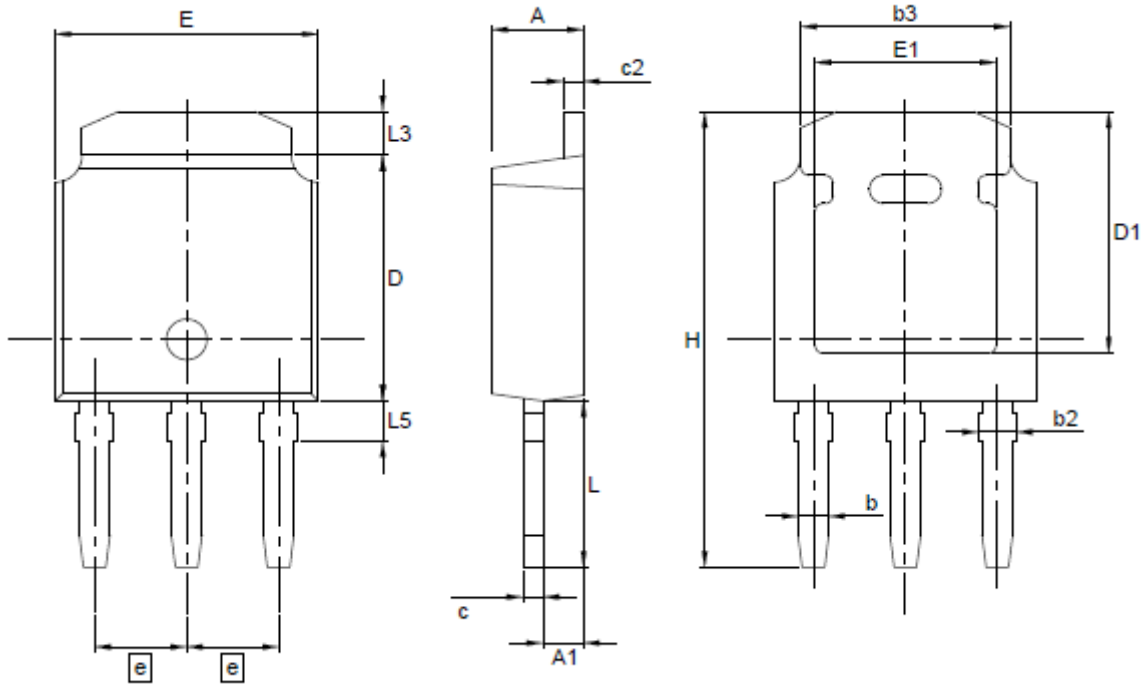


Fig.6 Body Diode Forward Voltage Variation with Source Current and Temperature



Package Dimension

TO251(VS)(IPAK(VS))




Note : Package body size, length and width do not include mold flash, protrusions and gate burrs

Symbol	Dimension (mm)		
	Min	Nom	Max
A	2.18	-	2.39
A1	0.89	-	1.15
b	0.64	-	0.89
b2	0.76	-	1.14
b3	4.95	-	5.46
c	0.40	-	0.61
c2	0.40	-	0.61
D	5.97	-	6.223
D1	5.10	-	-
e	2.286 BSC		
E	6.35	-	6.73
E1	4.32	-	-
H	10.26	-	11.45
L	3.98	-	4.28
L3	0.89	-	1.27
L5	-	-	1.23

DISCLAIMER:

The Products are not designed for use in hostile environments, including, without limitation, aircraft, nuclear power generation, medical appliances, and devices or systems in which malfunction of any Product can reasonably be expected to result in a personal injury. Seller's customers using or selling Seller's products for use in such applications do so at their own risk and agree to fully defend and indemnify Seller.

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